

NPN Power Transistors

These devices are high voltage, high speed transistors for horizontal deflection output stages of TV's and CRT's.

High Voltage: V_{CEV} = 330 or 400 V
 Fast Switching Speed: t_f = 750 ns (max)

• Low Saturation Voltage: $V_{CE(sat)} = 1 \text{ V (max)} @ 5 \text{ A}$

• Packaged in Compact JEDEC TO-220AB

MAXIMUM RATINGS

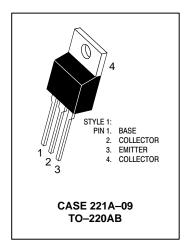
Rating	Symbol	BU406	BU407	Unit
Collector–Emitter Voltage	VCEO	200	150	Vdc
Collector–Emitter Voltage	VCEV	400	330	Vdc
Collector-Base Voltage	V _{CBO}	400	330	Vdc
Emitter Base Voltage	V _{EBO}	6		Vdc
Collector Current — Continuous Peak Repetitive Peak (10 ms)	lc	7 10 15		Adc
Base Current	ΙΒ	4		Adc
Total Device Dissipation, T _C = 25°C Derate above T _C = 25°C	PD	60 0.48		Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to 150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.08	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	70	°C/W
Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

BU406 BU407

7 AMPERES
NPN SILICON
POWER TRANSISTORS
60 WATTS
150 and 200 VOLTS



BU406 BU407

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage ⁽¹⁾ BU40 (IC = 100 mAdc, I _B = 0) BU40	OLO(303)	200 150	_ _	_ _	Vdc
Collector Cutoff Current (VCE = Rated VCEV, VBE = 0) (VCE = Rated VCEO + 50 Vdc, VBE = 0) (VCE = Rated VCEO + 50 Vdc, VBE = 0, TC = 150°C)	ICES	_ _ _	_ _ _	5 0.1 1	mAdc
Emitter Cutoff Current BU406, BU406 (VEB = 6 Vdc, IC = 0)	7 I _{EBO}	_	_	1	mAdc
ON CHARACTERISTICS (1)					
Collector–Emitter Saturation Voltage (I _C = 5 Adc, I _B = 0.5 Adc)	VCE(sat)	_	_	1	Vdc
Base–Emitter Saturation Voltage (I _C = 5 Adc, I _B = 0.5 Adc)	V _{BE} (sat)	_	_	1.2	Vdc
Forward Diode Voltage (I _{EC} = 5 Adc) "D" only	VEC	_	_	2	Volts
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f _{test} = 20 MHz)	f _T	10	_	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)	C _{ob}	_	80	_	pF
SWITCHING CHARACTERISTICS					
Inductive Load Crossover Time $(V_{CC} = 40 \text{ Vdc}, I_C = 5 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ Adc}, L = 150 \mu\text{H})$	t _C	_	_	0.75	μѕ

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1%.

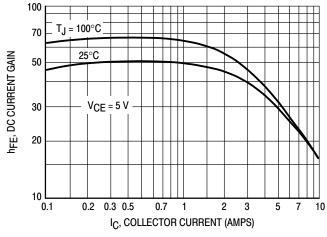


Figure 1. DC Current Gain

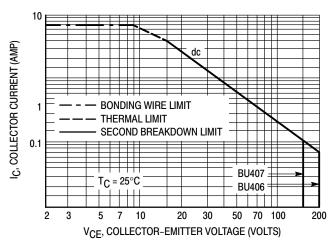
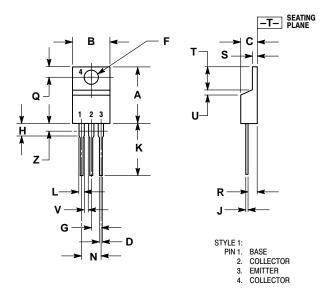


Figure 2. Maximum Rated Forward Bias Safe Operating Area

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PACKAGE DIMENSIONS

TO-220AB **CASE 221A-09 ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

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